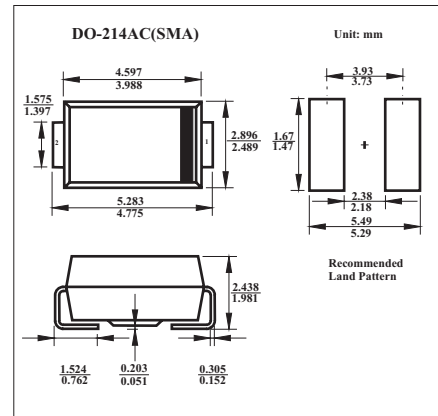


## KCD32 THRU KCD310 (SCD32 THRU SCD310)

### ■ Features

- For surface mounted applications.
- Low profile package.
- Built-in strain relief.
- Metal silicon junction, majority carrier conduction.
- Low power loss, high efficiency.
- High current capability, low forward voltage drop.
- High surge capability.



### ■ Absolute Maximum Ratings and Electrical Characteristics at 25°C

Parameter	Symbol	KCD32	KCD34	KCD36	KCD310	Unit
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	20	40	60	100	V
Maximum RMS voltage	V <sub>RMS</sub>	14	28	42	70	V
Maximum DC blocking voltage	V <sub>DC</sub>	20	40	60	100	V
Maximum average forward rectified current	I(AV)	3				A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	80				A
Maximum instantaneous forward voltage at 3.0A * 1	V <sub>F</sub>	0.5		0.7	0.85	V
Maximum DC reverse current * 1 T <sub>A</sub> =25°C at rated DC blocking voltage T <sub>A</sub> =100°C	I <sub>R</sub>	0.5				mA
		20		10		
Typical thermal resistance	R <sub>θJA</sub> R <sub>θJL</sub>	55 17				°C/W
Operating junction temperature range	T <sub>J</sub>	-55 to +125		-55 to +150		°C
Storage temperature range	T <sub>stg</sub>	-55 to +150				°C

\* 1. Pulse test: 300ms pulse width, 1% duty cycle.